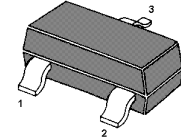
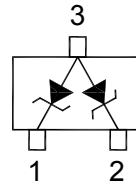


SAD500CA

Silicon Epitaxial Planar Diodes

Electrostatic Discharge Surge Absorber Diodes



1. Cathode 2. Cathode 3. Anode
Marking Code: **500**
SOT-23 Plastic Package

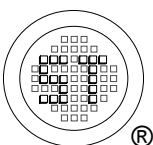
Absolute Maximum Ratings ($T_a = 25\text{ }^\circ\text{C}$)

Parameter	Symbol	Value	Unit
Power Dissipation	P_{tot}	200	mW
Surge Reverse Power ($t = 10\text{ }\mu\text{s}$, 1 Pulse)	P_{RSM}	2	W
Junction Temperature	T_j	150	$^\circ\text{C}$
Storage Temperature Range	T_{stg}	- 55 to + 150	$^\circ\text{C}$

Electrical Characteristics at $T_a = 25\text{ }^\circ\text{C}$

Parameter	Symbol	Min.	Typ.	Max.	Unit
Reverse Breakdown Voltage at $I_R = 1\text{ mA}$	$V_{(BR)R}$	5.3	8	-	V
Reverse Current at $V_R = 3\text{ V}$	I_R	-	-	0.1	μA
Total Capacitance at $V_R = 0\text{ V}$, $f = 1\text{ MHz}$	C_{tot}	-	3.5	-	pF
ESD Immunity Level ¹⁾ at $C = 150\text{ pF}$, $R = 330\text{ }\Omega$ (Contact Discharge)	-	8	-	-	KV

¹⁾ Biased Upon with IEC 61000-4-2.



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Dated : 29/07/2010 Rev:01

Figure1. I_{vs} .VBO CHARACTERISTICS

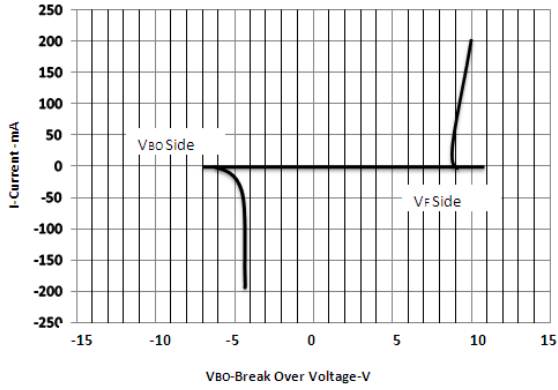


Figure 2. C_r vs. V CHARACTERISTICS

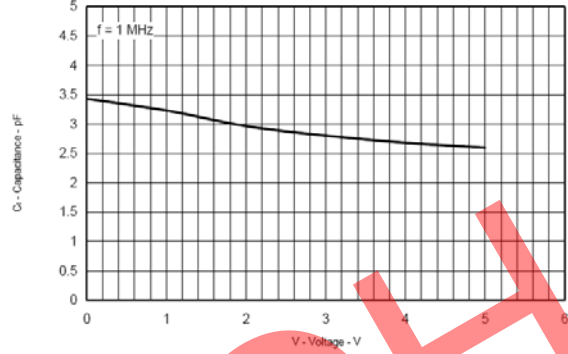
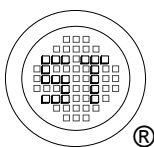


Figure3. I_t vs .V CHARACTERISTICS



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